5.0 V Micropower 150 mA LDO Linear Regulator with DELAY, Adjustable RESET, and Sense Output

The NCV4279A is a 5.0 V precision micropower voltage regulator with an output current capability of 150 mA.

The output voltage is accurate within $\pm 2.0\%$ with a maximum dropout voltage of 0.5 V at 100 mA. Low quiescent current is a feature drawing only 150 μ A with a 1.0 mA load. This part is ideal for any and all battery operated microprocessor equipment.

Microprocessor control logic includes an active reset output RO with delay and a SI/SO monitor which can be used to provide an early warning signal to the microprocessor of a potential impending reset signal. The use of the SI/SO monitor allows the microprocessor to finish any signal processing before the reset shuts the microprocessor down.

The active Reset circuit operates correctly at an output voltage as low as 1.0 V. The Reset function is activated during the power up sequence or during normal operation if the output voltage drops outside the regulation limits.

The reset threshold voltage can be decreased by the connection of an external resistor divider to the R_{ADJ} lead. The regulator is protected against reverse battery, short circuit, and thermal overload conditions. The device can withstand load dump transients making it suitable for use in automotive environments. The device has also been optimized for EMC conditions.

If the application requires pullup resistors at the logic outputs Reset and Sense Out, the NCV4269A with integrated resistors can be used.

Features

- $5.0 \text{ V} \pm 2.0\%$ Output
- Low 150 μA Quiescent Current
- Active Reset Output Low Down to $V_0 = 1.0 \text{ V}$
- Adjustable Reset Threshold
- 150 mA Output Current Capability
- Fault Protection
 - ♦ +60 V Peak Transient Voltage
 - ♦ -40 V Reverse Voltage
 - Short Circuit
 - Thermal Overload
- Early Warning through SI/SO Leads
- Internally Fused Leads in SO-14 Package
- Very Low Dropout Voltage
- Electrical Parameters Guaranteed Over Entire Temperature Range
- These are Pb-Free Devices
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

1



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

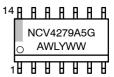


SO-8 D1 SUFFIX CASE 751





SO-14 D2 SUFFIX CASE 751A



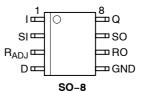
A = Assembly Location

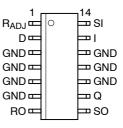
WL, L = Wafer Lot YY, Y = Year

WW, W = Work Week

, G = Lead Free Indicators

PIN CONNECTIONS





SO-14

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

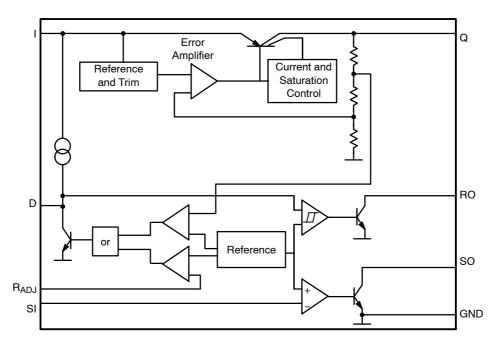


Figure 1. Block Diagram

PACKAGE PIN DESCRIPTION

Package Pin Number			
SO-8 SO-14 Pin Symbol		Pin Symbol	Function
3	1	R _{ADJ}	Reset Threshold Adjust; if not used to connect to GND.
4	2	D	Reset Delay; To Set Time Delay, Connect to GND with a Capacitor
5	3, 4, 5, 6, 10, 11, 12	GND	Ground
6	7	RO	Reset Output; This is an Open-Collector Output. Leave Open if Not Used.
7	8	SO	Sense Output; This is an Open-Collector Output. If not used, keep open.
8	9	Q	5 V Output; Connect to GND with a 10 μF Capacitor, ESR < 10 $\Omega.$
1	13	I	Input; Connect to GND Directly at the IC with a Ceramic Capacitor.
2	14	SI	Sense Input; If not used, Connect to Q.

MAXIMUM RATINGS ($T_J = -40^{\circ}C$ to $150^{\circ}C$)

Parameter	Symbol	Min	Max	Unit
Input to Regulator	V _I I _I	-40 Internally Limited	45 Internally Limited	V
Input Peak Transient Voltage	VI	-	60	V
Sense Input	V _{SI} I _{SI}	-40 -1	45 1	V mA
Reset Threshold Adjust	V _{RADJ} I _{RADJ}	-0.3 -10	7 10	V mA
Reset Delay	V _D I _D	-0.3 Internally Limited	7 Internally Limited	V
Ground	Iq	50	-	mA
Reset Output	V _{RO} I _{RO}	-0.3 Internally Limited	7 Internally Limited	٧
Sense Output	V _{SO} I _{SO}	-0.3 Internally Limited	7 Internally Limited	V
Regulated Output	V _Q I _Q	-0.5 -10	7.0 -	V mA
Junction Temperature Storage Temperature	T _J T _{STG}	- -50	150 150	°C °C
Input Voltage Operating Range Junction Temperature Operating Range	V _I T _J	- -40	45 150	°C V

LEAD TEMPERATURE SOLDERING AND MSL

Parameter	Symbol	Value	Unit
MSL, 8-Lead, 14-Lead, LS Temperature 260°C Peak (Notes 3)	MSL	1	-

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- This device series incorporates ESD protection and exceeds the following ratings: Human Body Model (HBM) ≤ 4.0 kV per AEC-Q100-002. Machine Model (MM) ≤ 200 V per AEC-Q100-003.
- 2. Latchup Current Maximum Rating: ≤ 150 mA per AEC-Q100-004.
- 3. Lead free: 60–150 Sec above 217°C, 40 Sec Max at Peak, 265°C Peak.

THERMAL CHARACTERISTICS

Characteristic	Test Conditions (Typical Values)	Unit
SO-8 Package (Note 4)		
Junction–to–Pin 4 (Ψ – JL4, Ψ_{L4})	53.8	°C/W
Junction-to-Ambient Thermal Resistance (R $_{\theta JA}$, θ_{JA})	170.9	°C/W
SO-14 Package (Note 4)		
Junction–to–Pin 4 (Ψ – JL4, Ψ_{L4})	18.4	°C/W
Junction-to-Ambient Thermal Resistance (R $_{\theta JA}$, θ_{JA})	111.6	°C/W

^{4. 2} oz copper, 50 mm² copper area, 1.5 mm thick FR4

ELECTRICAL CHARACTERISTICS ($-40^{\circ}C \le T_{J} \le 150^{\circ}C$, V_{I} = 13.5 V unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
REGULATOR						
Output Voltage	V _Q	$1 \text{ mA} \le I_Q \le 100 \text{ mA}; 6 \text{ V} \le V_I \le 16 \text{ V}$	4.90	5.00	5.10	V
Current Limit	IQ	-	150	200	500	mA
Current Consumption; $I_q = I_l - I_Q$	Iq	I _Q = 1 mA, RO, SO High	-	190	250	μΑ
Current Consumption; $I_q = I_l - I_Q$	Iq	I _Q = 1 mA, RO High, SO Low (Note 5)	-	560	650	μΑ
Current Consumption; $I_q = I_l - I_Q$	Iq	I _Q = 10 mA, RO, SO High	-	250	450	μΑ
Current Consumption; $I_q = I_l - I_Q$	Iq	I _Q = 50 mA, RO, SO High	-	2.0	3.0	mA
Dropout Voltage	V _{dr}	I _Q = 100 mA (Note 6)	-	0.25	0.5	V
Load Regulation	ΔV_{Q}	I _Q = 5 mA to 100 mA	-	10	20	mV
Line Regulation	ΔV_{Q}	V _I = 6 V to 26 V; I _Q = 1 mA	I	10	30	mV
RESET GENERATOR	-	•		•	-	-
Reset Switching Threshold	V _{RT}	-	4.50	4.65	4.80	٧
Reset Adjust Switching Threshold	V _{RADJ,TH}	V _Q > 3.5 V	1.26	1.35	1.44	٧
Reset Output Saturation Voltage	V _{RO,SAT}	$V_Q < V_{RT}$, $R_{RO} = 20 \text{ k}\Omega$	-	0.1	0.4	٧
Upper Delay Switching Threshold	V _{UD}	-	1.4	1.8	2.2	٧
Lower Delay Switching Threshold	V_{LD}	-	0.3	0.45	0.60	٧
Saturation Voltage on Delay Capacitor	V _{D,SAT}	V _Q < V _{RT}	-	-	0.1	V
Charge Current	I _D ,C	V _D = 1 V	3.0	6.5	9.5	μΑ
Delay Time L → H	t _d	C _D = 100 nF	17	28	_	ms
Delay Time H → L	t _{RR}	C _D = 100 nF	-	3.15	-	μs
INPUT VOLTAGE SENSE						
Sense Threshold High	V _{SI,High}	-	1.24	1.31	1.38	V
Sense Threshold Low	V _{SI,Low}	-	1.16	1.20	1.28	٧
Sense Output Saturation Voltage	V _{SO,Low}	V_{SI} < 1.20 V; V_{Q} > 3 V; R_{SO} = 20 k Ω	-	0.1	0.4	V
Sense Input Current	I _{SI}	-	-1.0	0.1	1.0	μΑ

Including 20 kΩ external SO pull–up resistor current.
 Dropout voltage = V_I – V_Q measured when the output voltage has dropped 100 mV from the nominal value obtained at 13.5 V input.

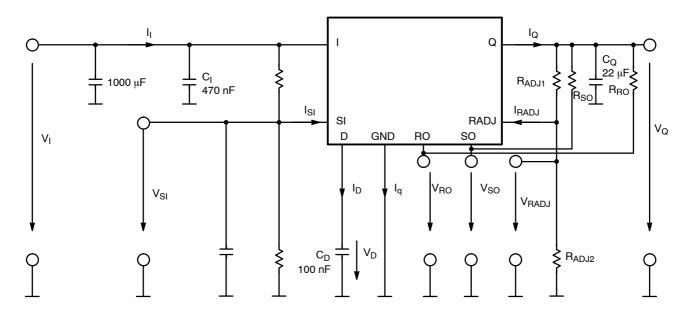


Figure 2. Measuring Circuit

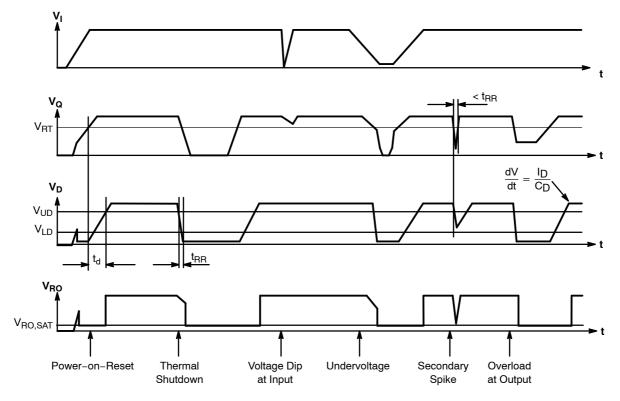


Figure 3. Reset Timing Diagram

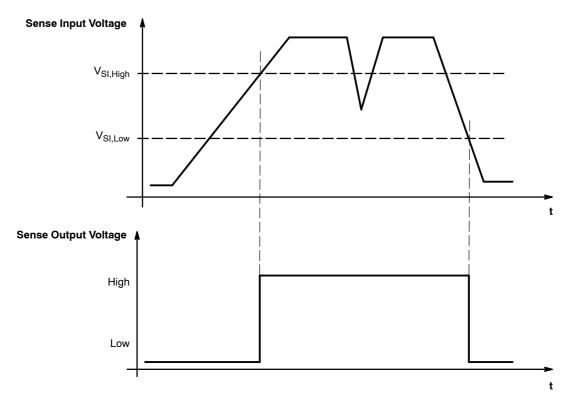
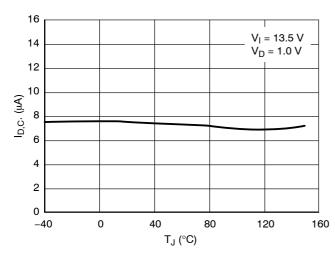


Figure 4. Sense Timing Diagram

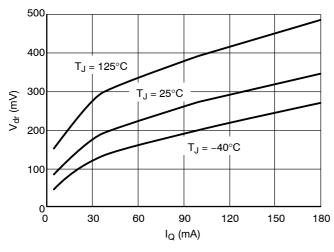
TYPICAL PERFORMANCE CHARACTERISTICS



3.2 $V_{I} = 13.5 \text{ V}$ 2.8 2.4 2.0 V_{UD} 1.6 1.2 8.0 V_{LD} 0.4 0 0 -40 40 80 120 160 T_J (°C)

Figure 5. Charge Current $I_{D,C}$ vs. Temperature T_{J}

Figure 6. Switching Voltage V_{UD} and V_{LD} vs. Temperature T_J



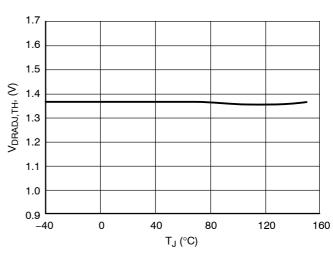
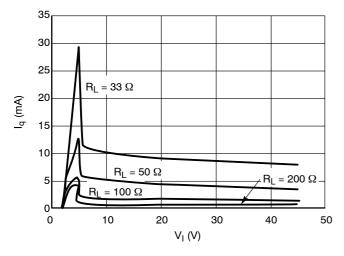


Figure 7. Drop Voltage V_{dr} vs. Output Current I_Q

Figure 8. Reset Adjust Switching Threshold $V_{RADJ,TH} \ vs. \ Temperature \ T_J$



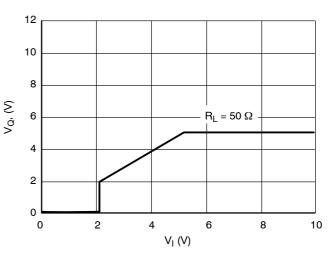
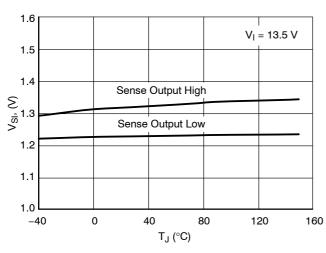


Figure 9. Current Consumption I_q vs. Input Voltage V_l

Figure 10. Output Voltage V_Q vs. Input Voltage V_I

TYPICAL PERFORMANCE CHARACTERISTICS



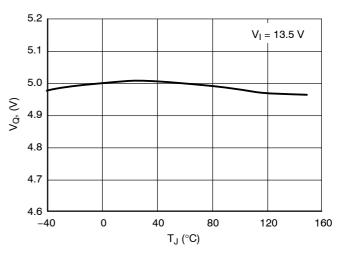


Figure 11. Sense Threshold V_{SI} vs. Temperature T_J

Figure 12. Output Voltage V_Q vs. Temperature T_J

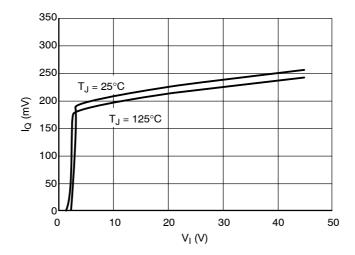
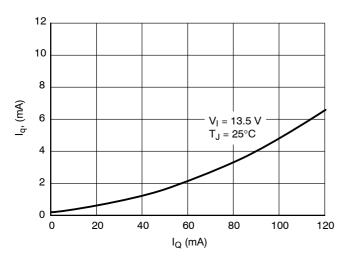


Figure 13. Output Current I_Q vs. Input Voltage V_I

TYPICAL PERFORMANCE CHARACTERISTICS



1.6 1.4 1.2 1.0 I_q, (mA) $V_{I} = 13.5 \text{ V}$ $T_J = 25^{\circ}C$ 0.8 0.6 0.4 0.2 0 L 10 30 50 I_Q (mA)

Figure 14. Current Consumption I_q vs. Output Current I_Q

Figure 15. Current Consumption I_q vs. Output Current I_Q

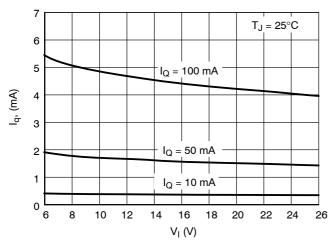


Figure 16. Current Consumption $\mathbf{I_q}$ vs. Input Voltage $\mathbf{V_l}$

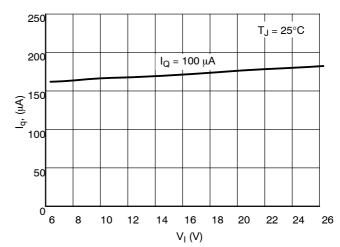


Figure 17. Current Consumption $\mathbf{I_q}$ vs. Input Voltage $\mathbf{V_l}$

TYPICAL THERMAL CHARACTERISTICS

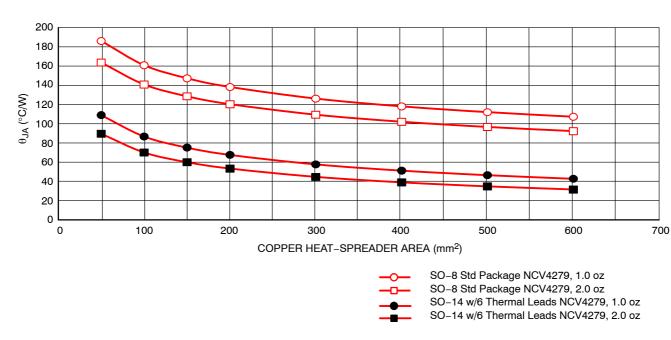


Figure 18. Junction–to–Ambient Thermal Resistance (θ_{JA}) vs. Heat Spreader Area

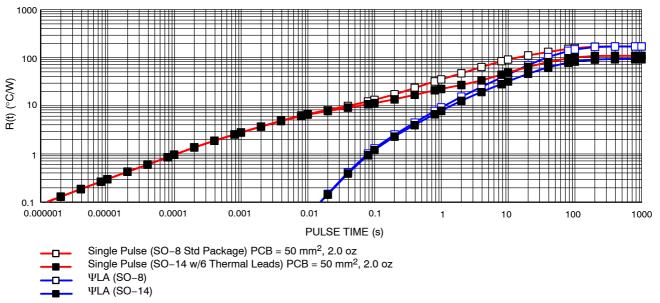


Figure 19. R(t) vs. Pulse Time

APPLICATION DESCRIPTION

OUTPUT REGULATOR

The output is controlled by a precision trimmed reference. The PNP output has drive quiescent current control for regulation while the input voltage is low, preventing over saturation. Current limit and voltage monitors complement the regulator design to give safe operating signals to the processor and control circuits.

RESET OUTPUT (RO)

A reset signal, Reset Output, RO, (low voltage) is generated as the IC powers up. After the output voltage V_Q increases above the reset threshold voltage V_{RT} , the delay timer D is started. When the voltage on the delay timer V_D passes V_{UD} , the reset signal RO goes high. A discharge of the delay timer V_D is started when V_Q drops and stays below the reset threshold voltage V_{RT} . When the voltage of the delay timer V_D drops below the lower threshold voltage V_{LD} the reset output voltage V_{RO} is brought low to reset the processor.

The reset output RO is an open collector NPN transistor, controlled by a low voltage detection circuit. The circuit is functionally independent of the rest of the IC, thereby guaranteeing that RO is valid for $V_{\rm O}$ as low as 1.0 V.

RESET ADJUST (RADJ)

The reset threshold V_{RT} can be decreased from a typical value of 4.65 V to as low as 3.5 V by using an external voltage divider connected from the Q lead to the pin RADJ, as shown in Figure 20. The resistor divider keeps the voltage above the $V_{RADJ,TH}$ (typical 1.35 V) for the desired input voltages, and overrides the internal threshold detector. Adjust the voltage divider according to the following relationship:

$$V_{RT} = V_{RADJ,TH} \cdot (R_{ADJ1} + R_{ADJ2}) / R_{ADJ2}$$
 (eq. 1)

If the reset adjust option is not needed, the R_{ADJ} pin should be connected to GND causing the reset threshold to go to its default value (typically 4.65 V).

RESET DELAY (D)

The reset delay circuit provides a delay (programmable by capacitor C_D) on the reset output lead RO. The delay lead D provides charge current $I_{D,C}$ (typically 6.5 μ A) to the external delay capacitor C_D during the following times:

- 1. During Powerup (once the regulation threshold has been exceeded).
- 2. After a reset event has occurred and the device is back in regulation. The delay capacitor is set to discharge when the regulation (V_{RT} , reset threshold voltage) has been violated. When the delay capacitor discharges to V_{LD} , the reset signal RO pulls low.

SETTING THE DELAY TIME

The delay time is set by the delay capacitor C_D and the charge current I_D . The time is measured by the delay capacitor voltage charging from the low level of V_{DSAT} to the higher level V_{UD} . The time delay follows the equation:

$$t_d = [C_D (V_{UD} - V_{D,SAT})]/I_D$$
 (eq. 2)

Example:

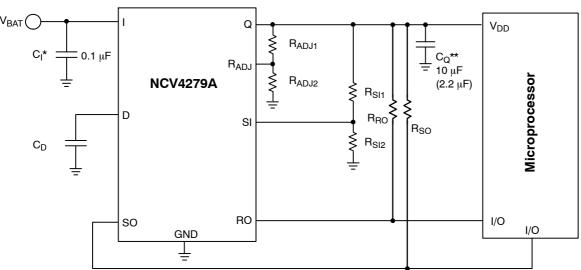
Using $C_D = 100 \text{ nF}$.

Use the typical value for $V_{D,SAT} = 0.1 \text{ V}$.

Use the typical value for $V_{\rm UD} = 1.8 \text{ V}$.

Use the typical value for Delay Charge Current $I_D = 6.5 \mu A$.

$$t_d = [100 \text{ nF} (1.8 - 0.1 \text{ V})]/6.5 \,\mu\text{A} = 26.2 \text{ ms} \quad (eq. 3)$$



^{*}C_I required if regulator is located far from the power supply filter.

Figure 20. Application Diagram

^{**} C_Q – minimum cap required for stability is 2.2 μ F while higher over/under–shoots may be expected. Cap must operate at required temperature range.

SENSE INPUT (SI) / SENSE OUTPUT (SO) VOLTAGE MONITOR

An on-chip comparator is available to provide early warning to the microprocessor of a possible reset signal. The output is from an open collector driver. The reset signal typically turns the microprocessor off instantaneously. This can cause unpredictable results with the microprocessor. The signal received from the SO pin will allow the microprocessor time to complete its present task before shutting down. This function is performed by a comparator referenced to the band gap voltage. The actual trip point can be programmed externally using a resistor divider to the input monitor SI (Figure 20). The values for $R_{\rm SI1}$ and $R_{\rm SI2}$ are selected for a typical threshold of 1.20 V on the SI Pin.

SIGNAL OUTPUT

Figure 21 shows the SO Monitor timing waveforms as a result of the circuit depicted in Figure 20. As the output voltage (V_Q) falls, the monitor threshold (V_{SILOW}), is crossed. This causes the voltage on the SO output to go low sending a warning signal to the microprocessor that a reset signal may occur in a short period of time. $T_{WARNING}$ is the time the microprocessor has to complete the function it is currently working on and get ready for the reset shutdown signal. When the voltage on the SO goes low and the RO stays high the current consumption is typically 560 μ A at 1 mA load current.

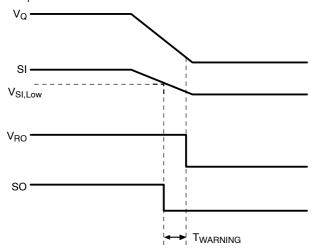


Figure 21. SO Warning Waveform Time Diagram

STABILITY CONSIDERATIONS

The input capacitor C_I in Figure 20 is necessary for compensating input line reactance. Possible oscillations caused by input inductance and input capacitance can be damped by using a resistor of approximately $1.0\ \Omega$ in series with C_I

The output or compensation capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability.

The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive

solution, but, if the circuit operates at low temperatures $(-25^{\circ}\text{C to } -40^{\circ}\text{C})$, both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The 10 μF output capacitor C_Q shown in Figure 20 should work for most applications; however, it is not necessarily the optimized solution. Stability is guaranteed at CQ is min 2.2 μF and max ESR is 10 Ω . There is no min ESR limit which was proved with MURATA's ceramic caps GRM31MR71A225KA01 (2.2 μF , 10 V, X7R, 1206) and GRM31CR71A106KA01 (10 μF , 10 V, X7R, 1206) directly soldered between output and ground pins.

CALCULATING POWER DISSIPATION IN A SINGLE OUTPUT LINEAR REGULATOR

The maximum power dissipation for a single output regulator (Figure 20) is:

 $P_{D(max)} = [V_{I(max)} - V_{Q(min)}]I_{Q(max)} + V_{I(max)}I_{q} \text{ (eq. 4)}$

where:

 $V_{I(max)}$ is the maximum input voltage,

 $V_{Q(min)}$ is the minimum output voltage,

 $I_{Q(max)}$ is the maximum output current for the application, and I_q is the quiescent current the regulator consumes at $I_{Q(max)}$.

Once the value of $P_{D(max)}$ is known, the maximum permissible value of $R_{\theta JA}$ can be calculated:

$$R_{\theta JA} = (150^{\circ}C - T_{A}) / P_{D}$$
 (eq. 5)

The value of $R_{\theta JA}$ can then be compared with those in the package section of the data sheet. Those packages with $R_{\theta JA}$'s less than the calculated value in equation 2 will keep the die temperature below 150°C. In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heatsink will be required. The current flow and voltages are shown in the Measurement Circuit Diagram.

HEATSINKS

A heatsink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of $R_{\theta JA}$:

$$R_{\theta}JA = R_{\theta}JC + R_{\theta}CS + R_{\theta}SA$$
 (eq. 6)

where:

 $R_{\theta JC}$ = the junction-to-case thermal resistance,

 $R_{\theta CS}$ = the case-to-heat sink thermal resistance, and

 $R_{\theta SA}$ = the heat sink-to-ambient thermal resistance.

 $R_{\theta JC}$ appears in the package section of the data sheet. Like $R_{\theta JA}$, it too is a function of package type, $R_{\theta CS}$ and $R_{\theta SA}$ are functions of the package type, heatsink and the interface between them. These values appear in data sheets of heatsink manufacturers. Thermal, mounting, and heatsinking considerations are discussed in the ON Semiconductor application note AN1040/D, available on the ON Semiconductor website.

ORDERING INFORMATION

Device	Output Voltage	Package	Shipping [†]
NCV4279A50D1G		SO-8 (Pb-Free)	98 Units/Rail
NCV4279A50D1R2G		SO-8 (Pb-Free)	2500 Tape & Reel
NCV4279A50D2G	5.0 V	SO-14 (Pb-Free)	55 Units/Rail
NCV4279A50D2R2G		SO-14 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications,including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



XS

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	1.27 BSC		0 BSC
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

0.25 (0.010) M Z Y S



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week W = Pb-Free Package

XXXXXX XXXXXX AYWW AYWW H \mathbb{H} Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α

ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2

onsemi and ONSEMI. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 3:

STYLE 2:

DATE 16 FEB 2011

STYLE 4:

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE
8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	8. EMITTER, #1 STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	8. COMMON CATHODE STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

DOCUMENT NUMBER:	98ASB42564B	Printed versions are uncontrolled except when accessed directly from the Document Heposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

STYLE 1:





△ 0.10

SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIM	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2

onsemi and ONSEMI. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales